
2SB1407(L)/(S)

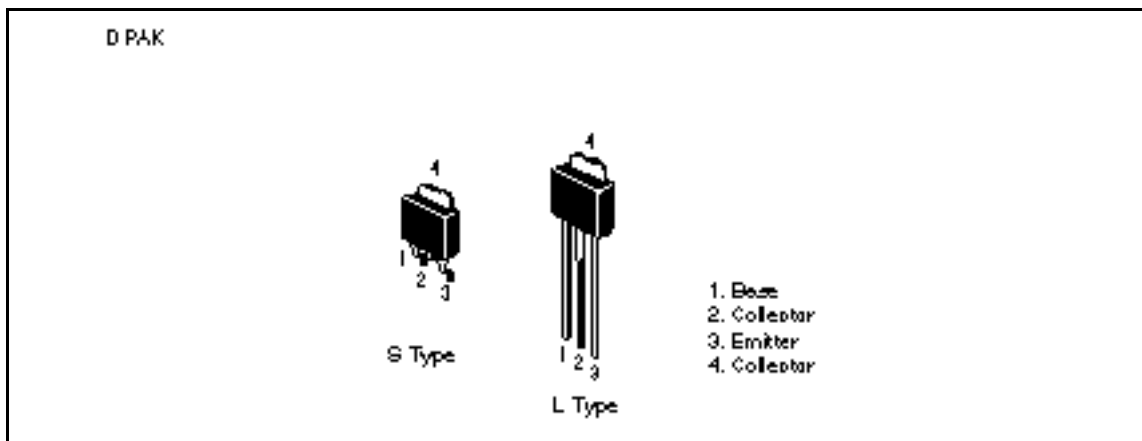
Silicon PNP Epitaxial

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Application

Low frequency power amplifier complementary Pair with 2SD2121(L)/(S)

Outline



2SB1407(L)/(S)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-35	V
Collector to emitter voltage	V_{CEO}	-35	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-2.5	A
Collector peak current	$I_{C(\text{peak})}$	-3	A
Collector power dissipation	P_C^{*1}	18	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Note: 1. Value at $T_C = 25^\circ\text{C}$.

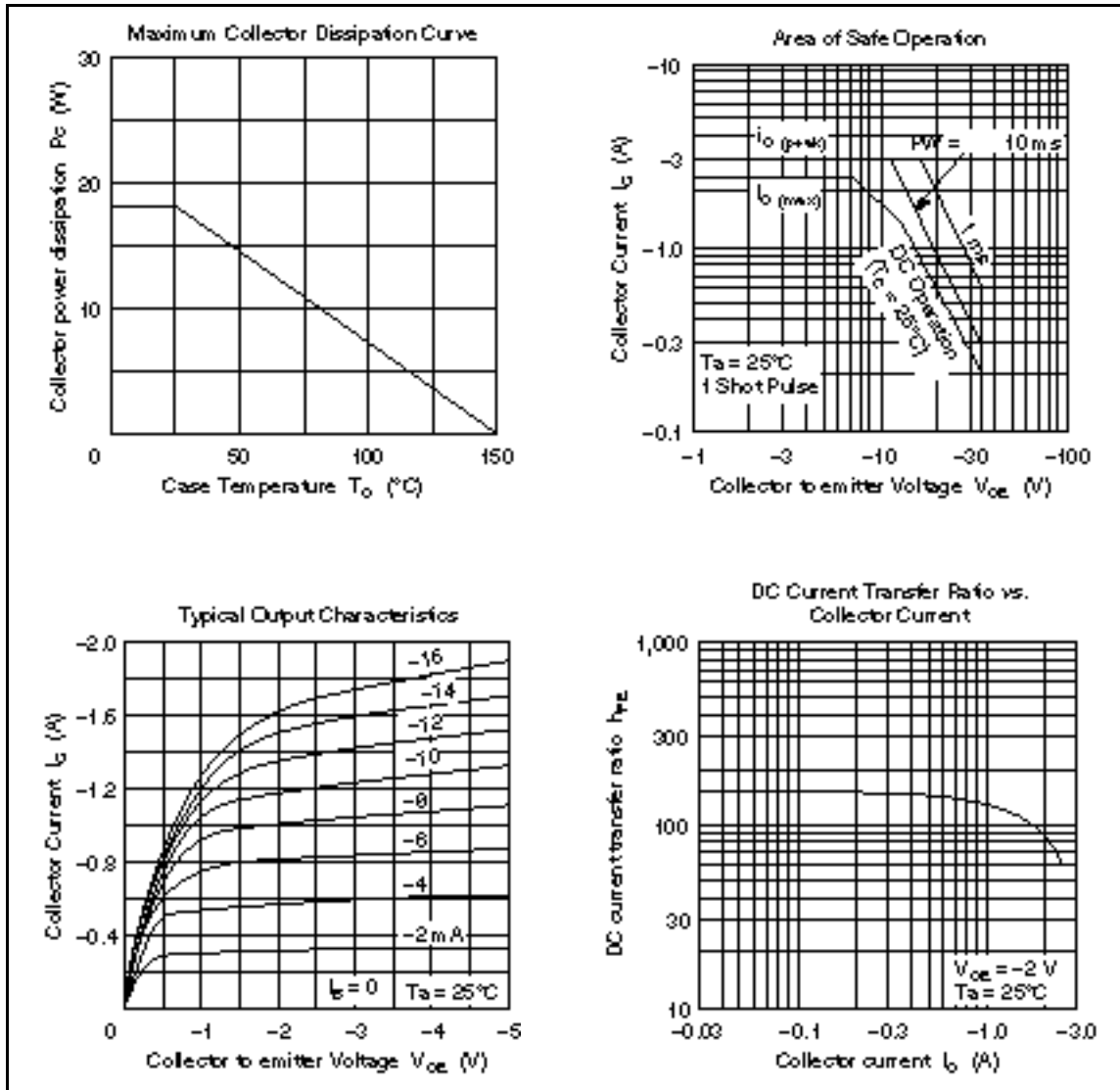
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-35	—	—	V	$I_C = -1 \text{ mA}, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-35	—	—	V	$I_C = -10 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	V	$I_E = -1 \text{ mA}, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-20	μA	$V_{CB} = -35 \text{ V}, I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	320		$V_{CE} = -2 \text{ V}, I_C = -0.5 \text{ A}^{*2}$
	h_{FE2}	20	—	—		$V_{CE} = -2 \text{ V}, I_C = -1.5 \text{ A}^{*2}$
Base to emitter voltage	V_{BE}	—	—	-1.5	V	$V_{CE} = -2 \text{ V}, I_C = -1.5 \text{ A}^{*2}$
Collector to emitter saturation voltage	$V_{CE(\text{sat})}$	—	—	-1.0	V	$I_C = -2 \text{ A}, I_B = -0.2 \text{ A}^{*2}$

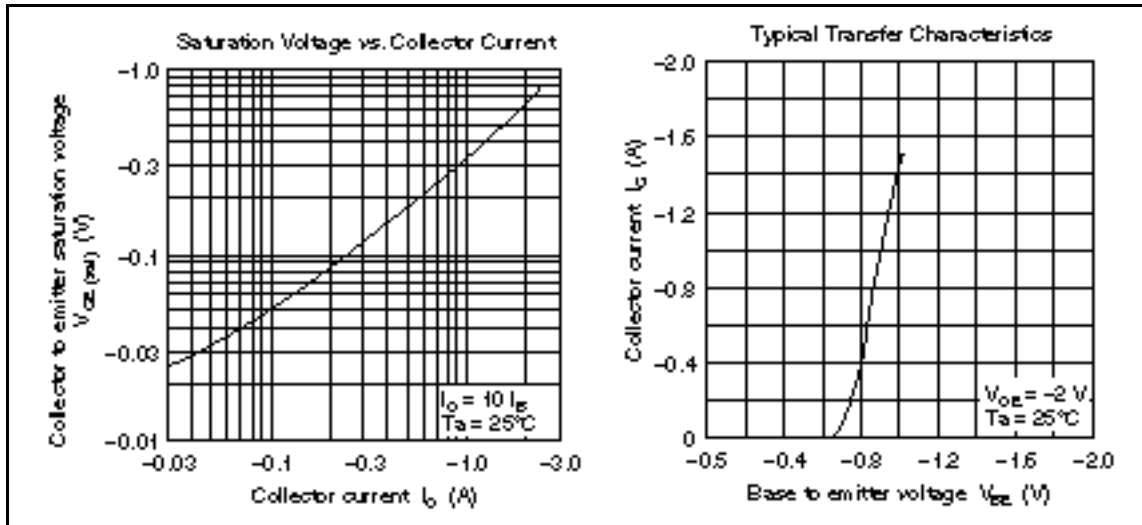
Notes: 1. The 2SB1407(L)/(S) is grouped by h_{FE1} as follows.

B	C	D
60 to 120	100 to 200	160 to 320

2. Pulse test.



2SB1407(L)/(S)



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